

製品概要

NSS20201L: Low $V_{CE(sat)}$ Transistor, NPN, 20 V, 4.0 A

技術情報は、データシートをご参照ください。

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

特長

- High Current, Low $V_{CE(sat)}$, ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

利点

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

アプリケーション

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

電氣的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}^{at} Max$ (V)	I_C Cont. (A)	$V_{CEO} Min$ (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(0)}$ (V)	$h_{FE} Min$	$h_{FE} Max$	f_T Min (MHz)	$P_{TM} Max$ (W)	Package Type
NSS20201LT1G	0.1096	Pb-free Halide free	Active	NPN	Low $V_{CE(sat)}$	0.05	2	20	20	6	0.9	0.9	200	-	150	0.54	SOT-23-3
NSV20201LT1G	0.1481	AEC Qualified PPAP Capable Pb-free Halide free	Active	NPN	Low $V_{CE(sat)}$	0.05	2	20	20	6	0.9	0.9	200	-	150	0.54	SOT-23-3

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

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